

Silicon PNP Power Transistors

2SB1393 2SB1393A

DESCRIPTION

- With TO-220Fa package
- Satisfactory linearity of h_{FE}
- Low collector to emitter saturation voltage
- Complement to type 2SD1985/1985A

APPLICATIONS

- For power amplification

PINNING

| PIN | DESCRIPTION |
|-----|-------------|
| 1 | Base |
| 2 | Collector |
| 3 | Emitter |

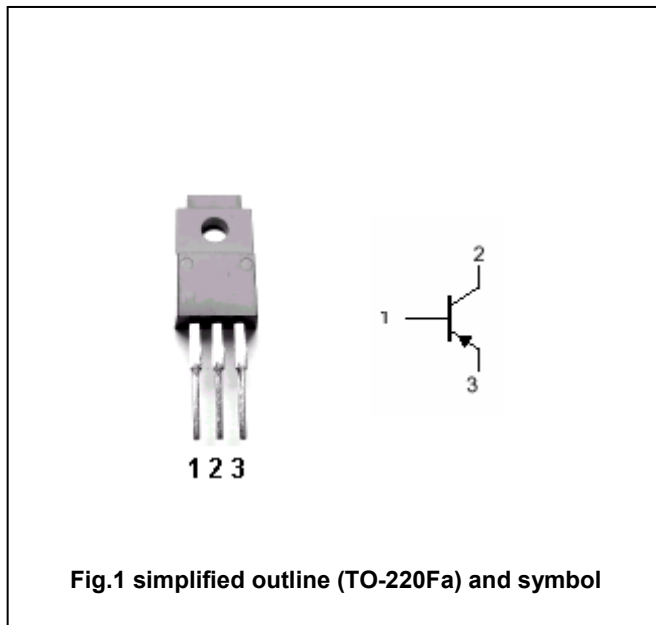


Fig.1 simplified outline (TO-220Fa) and symbol

Absolute maximum ratings($T_a=25^\circ C$)

| SYMBOL | PARAMETER | CONDITIONS | VALUE | UNIT |
|-----------|-----------------------------|------------------|---------|------------|
| V_{CBO} | Collector-base voltage | 2SB1393 | -60 | V |
| | | 2SB1393A | -80 | |
| V_{CEO} | Collector-emitter voltage | 2SB1393 | -60 | V |
| | | 2SB1393A | -80 | |
| V_{EBO} | Emitter-base voltage | Open collector | -5 | V |
| I_C | Collector current (DC) | | -3 | A |
| I_{CM} | Collector current-Peak | | -5 | A |
| P_C | Collector power dissipation | $T_c=25^\circ C$ | 25 | W |
| | | $T_a=25^\circ C$ | 2 | |
| T_j | Junction temperature | | 150 | $^\circ C$ |
| T_{stg} | Storage temperature | | -55~150 | $^\circ C$ |

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CHARACTERISTICS

T_j=25 °C unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | TYP. | MAX | UNIT |
|----------------------|--------------------------------------|---|---|---|------|------|
| V _{(BR)CEO} | Collector-emitter breakdown voltage | 2SB1393 | I _C =-30mA, I _B =0 | -60 | | V |
| | | 2SB1393A | | -80 | | |
| V _{CEsat} | Collector-emitter saturation voltage | I _C =-3A; I _B =-0.375A | | | -1.2 | V |
| V _{BE} | Base-emitter voltage | V _{CE} =-4V; I _C =-3A | | | -1.8 | V |
| I _{CES} | Collector cut-off current | 2SB1393 | V _{CE} =-60V; V _{BE} =0 | | | μA |
| | | 2SB1393A | | V _{CE} =-80V; V _{BE} =0 | | |
| I _{CEO} | Collector cut-off current | 2SB1393 | V _{CE} =-30V; I _B =0 | | | μA |
| | | 2SB1393A | | V _{CE} =-60V; I _B =0 | | |
| I _{EBO} | Emitter cut-off current | V _{EB} =-5V; I _C =0 | | | -1.0 | mA |
| h _{FE-1} | DC current gain | I _C =-1A; V _{CE} =-4V | 70 | | 250 | |
| h _{FE-2} | DC current gain | I _C =-3A; V _{CE} =-4V | 10 | | | |
| f _T | Transition frequency | I _C =-0.1A; V _{CE} =-5V; f=1MHz | | 20 | | MHz |

Switching times

| | | | | | | |
|-----------------|--------------|---|--|-----|--|----|
| t _{on} | Turn-on time | I _C =-1A; I _{B1} =-0.1A I _{B2} =0.1A; V _{CC} =-50V | | 0.5 | | μs |
| t _s | Storage time | | | 1.2 | | μs |
| t _f | Fall time | | | 0.3 | | μs |

◆ h_{FE-1} Classifications

| Q | P |
|--------|---------|
| 70-150 | 120-250 |

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PACKAGE OUTLINE

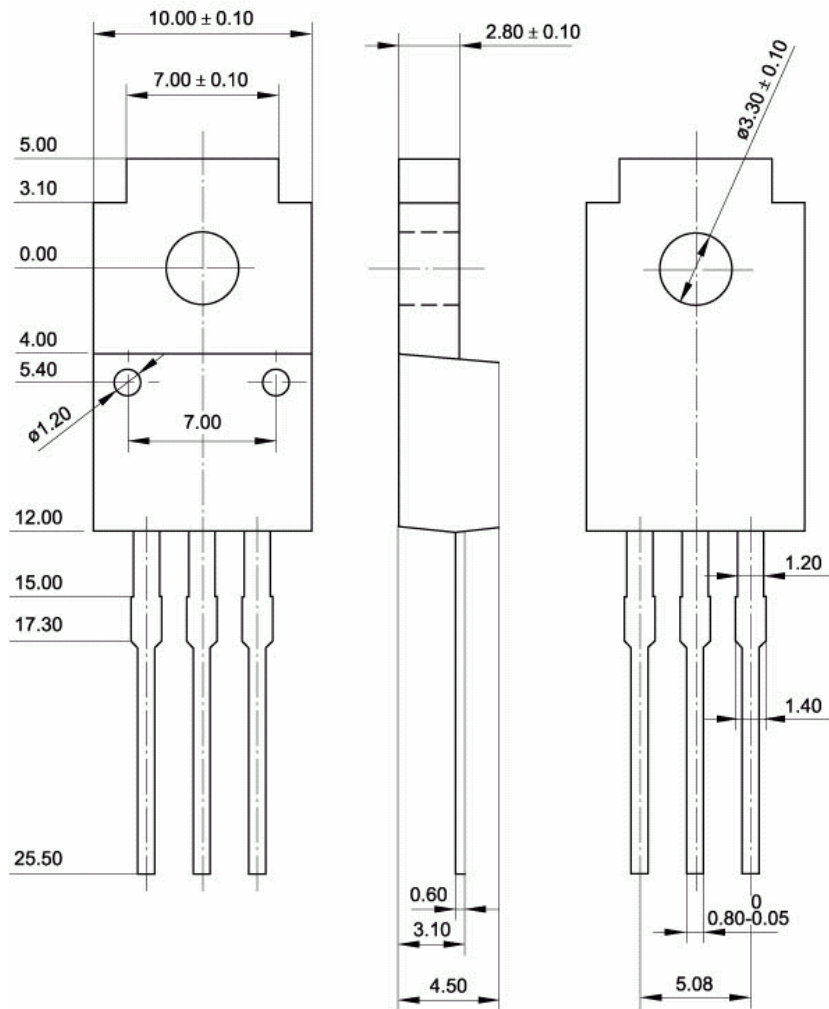


Fig.2 Outline dimensions (unindicated tolerance: ± 0.15 mm)

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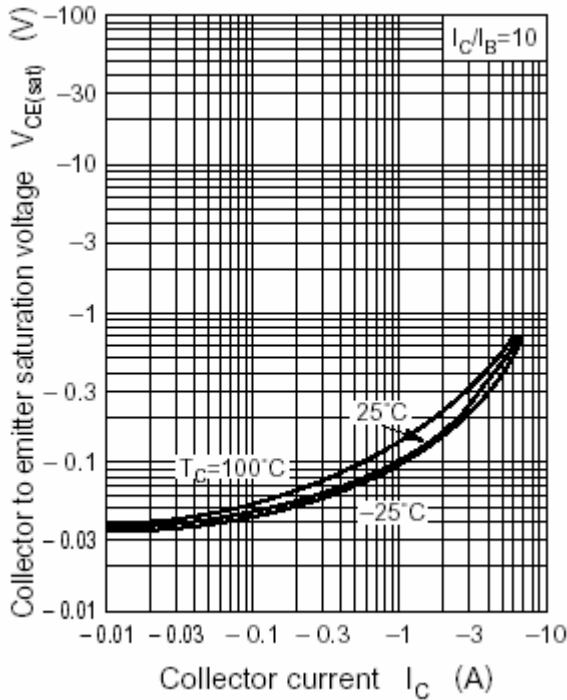


Fig.3 Collector-Emitter Saturation Voltage

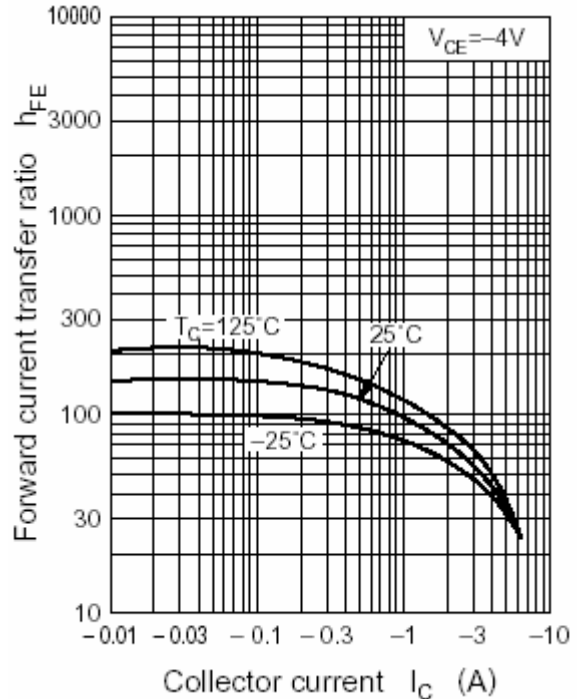


Fig.4 DC current Gain

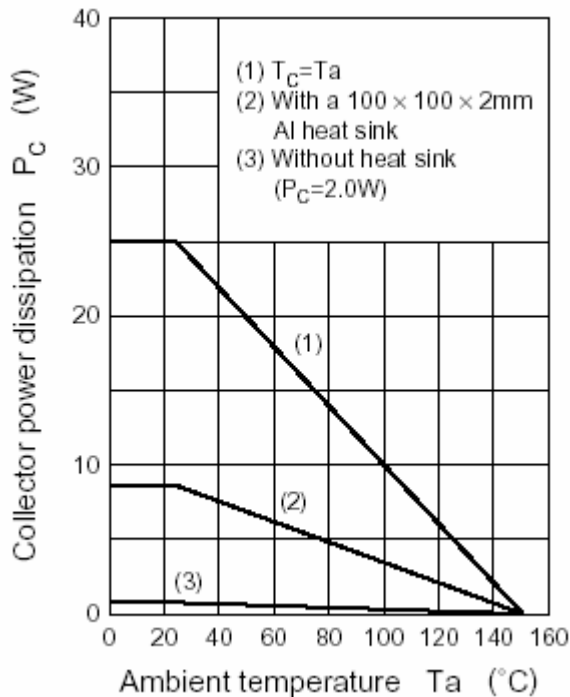


Fig.5 P_C - T_a Derating

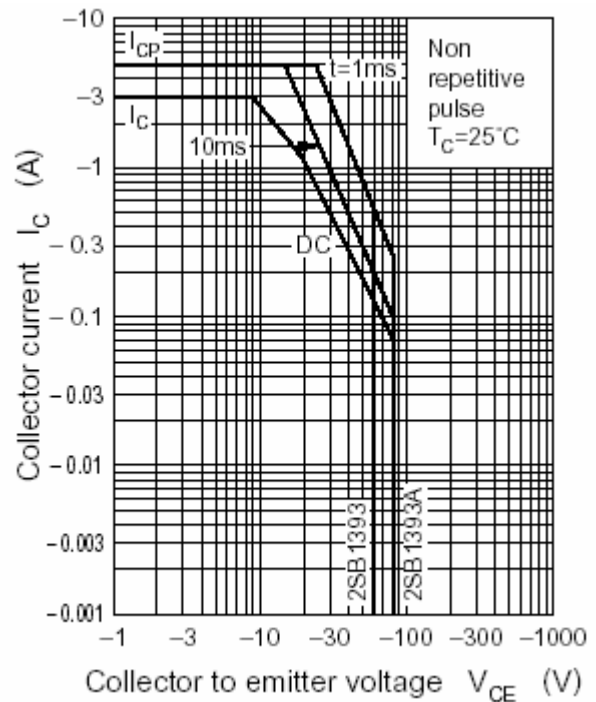


Fig.6 Safe Operating Area